General Purpose Transistors

NPN Silicon

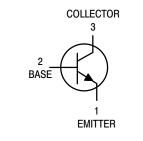
Features

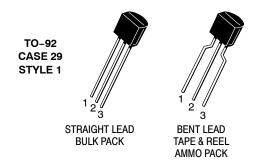
• Pb-Free Packages are Available*



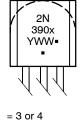
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAMS



Y = Year WW = Work Week

х

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	۱ _C	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 2) (I_{C} = 1.0 mAdc, I_{B} = 0)		V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu Adc, I_E = 0$)		V _{(BR)CBO}	60	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (Note 2) (I _C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	2N3903 2N3904	h _{FE}	20 40	_	-
(I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc)	2N3903		35	_	
$(I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3904 2N3903 2N3904		70 50 100	- 150 300	
$(I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3903 2N3904		30 60	-	
$(I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3904 2N3903 2N3904		15 30		
		V _{CE(sat)}		0.2 0.3	Vdc
Base – Emitter Saturation Voltage (Note 2) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)		V _{BE(sat)}	0.65	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	2N3903 2N3904	fT	250 300		MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻¹
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	2N3903 2N3904	h _{fe}	50 100	200 400	-
Output Admittance ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmho
Noise Figure (I_C = 100 $\mu \text{Adc}, \text{V}_{\text{CE}}$ = 5.0 Vdc, R_S = 1.0 k Ω, f = 1.0 kHz)	2N3903 2N3904	NF		6.0 5.0	dB
SWITCHING CHARACTERISTICS	1				
Delay Time (V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	_	35	ns
Rise Time $I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc}$	ľ	t _r	-	35	ns

	Fall Time			
2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2%.				

 $\begin{array}{l} (V_{CC} = 3.0 \; Vdc, \; I_{C} = 10 \; mAdc, \\ I_{B1} = I_{B2} = 1.0 \; mAdc) \end{array}$

2N3903 2N3904

t_s

t_f

175

200

50

ns

ns

-

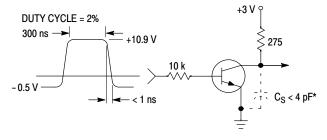
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Storage Time

ORDERING INFORMATION

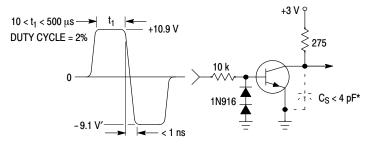
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO–92 (Pb–Free)	2000 / Ammo Pack

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

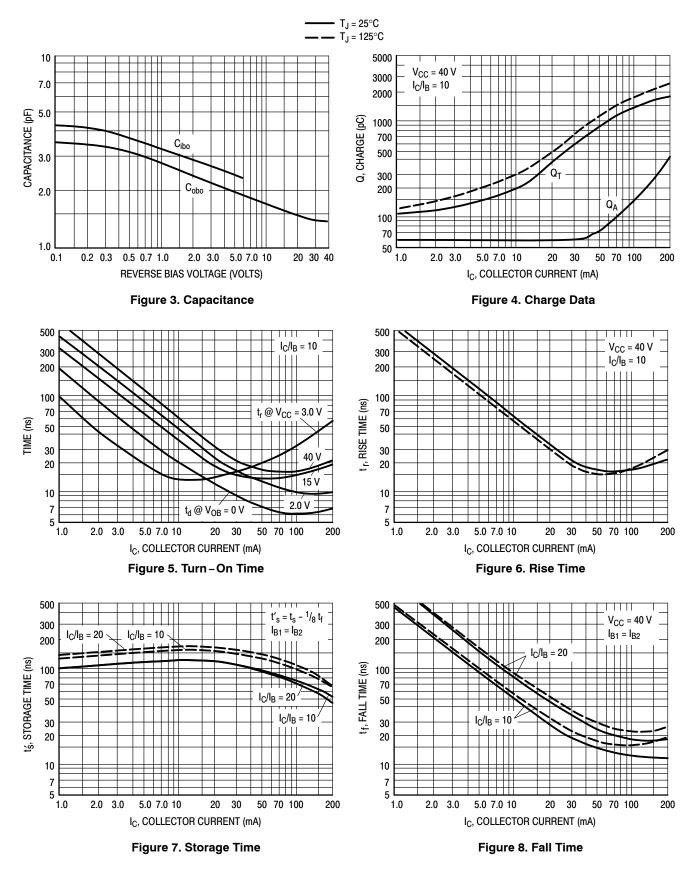
Figure 1. Delay and Rise Time Equivalent Test Circuit

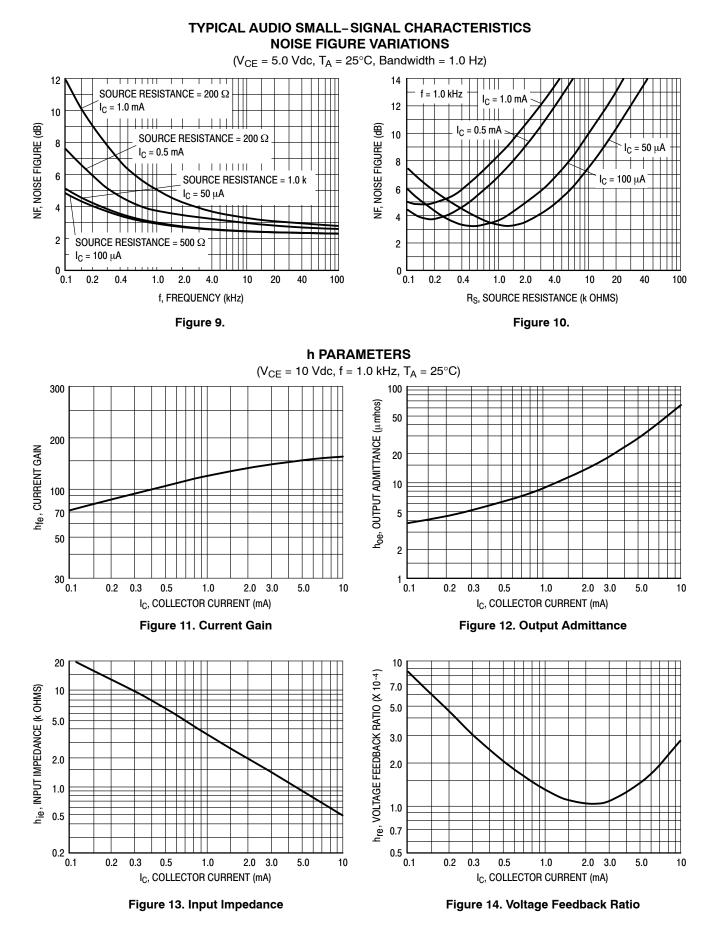


* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

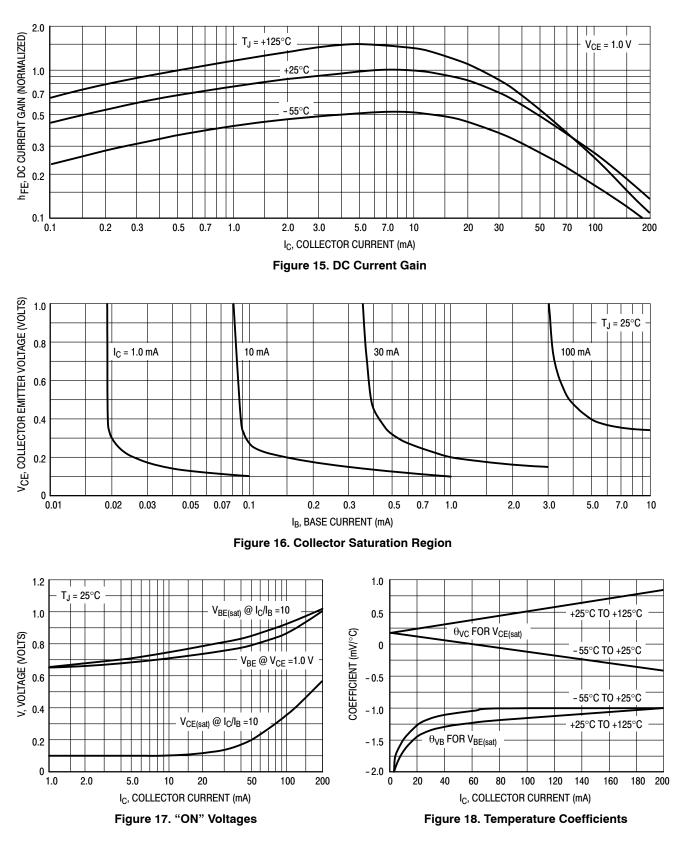
TYPICAL TRANSIENT CHARACTERISTICS





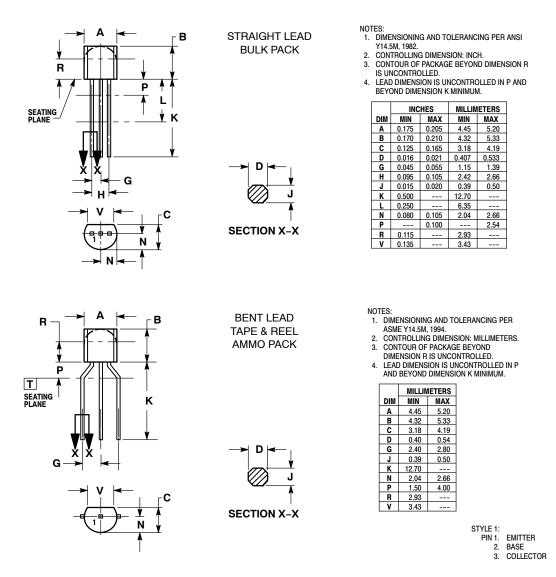
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TYPICAL STATIC CHARACTERISTICS



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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